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Substitute for form 1449A/PTO (Modified by BSTZ 6/30/99)  <b>INFORMATION DISCLOSURE          STATEMENT BY APPLICANT</b>  <i>(use as many sheets as necessary)</i>			<b>Complete if Known</b>		
			Application Number	New Application	
			Filing Date	Herewith	
			First Named Inventor	Jack Zezhong Peng	
			Group Art Unit	Not yet assigned	
Examiner Name	Not yet assigned				
Attorney Docket Number	005819.P001				
Sheet	1	of	1		

1000 U.S. PTO  
 09/955641  
 09/18/01


U.S. PATENT DOCUMENTS				
Examiner Initials *	U.S. Patent Document Number	Name of Patentee or Applicant of Cited Document	Date of Publication of Cited Document MM-DD-YYYY	Filing Date if Appropriate

FOREIGN PATENT DOCUMENTS							
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OTHER DOCUMENTS		
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HN	✓ MIRANDA, ENRIQUE et al; Analytic Modeling of Leakage Current Through Multiple Breakdown Paths in SiO <sub>2</sub> Films; 39th Annual International Reliability Physics Symposium; Orlando, FL 2001	
HN	✓ LOMBARDO, S. et al; Softening of Breakdown in Ultra-Thin Gate Oxide nMOSFET's at Low Inversion Layer Density; 39th Annual International Reliability Physics Symposium; Orlando, FL 2001	
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Examiner Signature	HIEN NGUYEN	Date Considered	4/29/04
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\*EXAMINER: Initial if reference considered, whether or not citation is in conformance with MPEP 609. Draw line through citation if not in conformance and not considered. Include copy of this form with next communication to applicant.

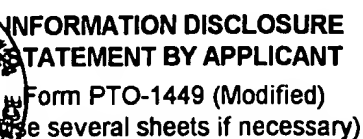
<b>INFORMATION DISCLOSURE STATEMENT BY APPLICANT</b> Form PTO-1449 (Modified) (Use several sheets if necessary)				<b>COMPLETE IF KNOWN</b>	
				Application Number	09/955,641
				Confirmation Number	1777
				Filing Date	09/18/2001
				First Named Inventor	Jack Zezhong Peng
				Group Art Unit	2818
				Examiner Name	
Sheet	1	of	1	Attorney Docket No.	384848001US

U.S. PATENT DOCUMENTS						
Examiner Initials	Cite No.	U.S. Patent or Application		Name of Patentee or Inventor of Cited Document	Date of Publication or Filing Date of Cited Document	Pages, Columns, Lines, Where Relevant Figures Appear
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Form PTO-1449 (Modified)  
Use several sheets if necessary)

Application Number	09/955,641
Confirmation Number	1777
Filing Date	09/18/2001
First Named Inventor	Jack Zezhong Peng
Group Art Unit	2818 <i>2824</i>
Examiner Name	
Attorney Docket No.	384848001US


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4/29/04

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09/955641

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Page 1 of 2

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## Signature

Examiner Name	Date
H. NGUYEN	4/29/04

# Electronic Information Disclosure Statement



## SEMICONDUCTOR MEMORY CELL AND MEMORY ARRAY USING A BREAKDOWN PHENOMENA IN AN ULTRA-THIN DIELECTRIC

Application:



09/955641

Confirmation:

1777

Applicant(s):

Jack Peng

Docket Number:

384848001.US

Group Art Unit:

2824

Examiner:

Hien N. Nguyen

search string:

( 4677742 or 4599705 ).pn.

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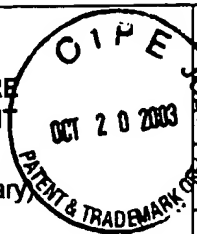
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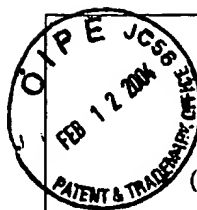
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Group Art Unit 2818  
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Attorney Docket No. 38484800109

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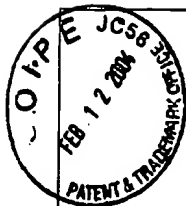
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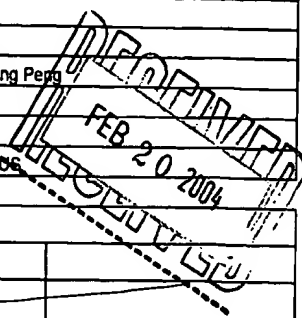
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Sheet 2 of 2

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Application Number	09/955,641
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First Named Inventor	Jack Zezhong Peng
Group Art Unit	2818
Examiner Name	
Attorney Docket No.	384848001

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